

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|------------------|
| - | 997 | 257/57 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/22 11:48 |
| - | 1675 | 257/59 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:24 |
| - | 1323 | 257/72 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:10 |
| - | 80 | 438/609 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:10 |
| - | 682 | 438/149 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:11 |
| - | 96 | 438/341 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:11 |
| - | 173 | 437/181 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:11 |
| - | 349 | 438/48 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:11 |
| - | 1641 | 438/128 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:12 |
| - | 863 | 438/151 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:13 |
| - | 207 | 438/157 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:13 |
| - | 636 | 438/166 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:13 |
| - | 889 | 257/59 and transparent and (thin adj film adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/10/23 09:19 |
| - | 1 | 257/581 and transparent and (thin adj film adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:38 |

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| - | 67 | 257/59 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:55 |
| - | 45 | 257/72 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/10/23 17:49 |
| - | 13 | 257/57 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/19 15:12 |
| - | 1 | 257/359 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:55 |
| - | 5 | 437/181 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:56 |
| - | 1 | 438/609 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:56 |
| - | 8 | 438/149 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:56 |
| - | 1 | 438/48 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 17:56 |
| - | 1 | 438/128 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/18 07:40 |
| - | 11 | 438/151 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 18:21 |
| - | 3 | 438/157 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 18:09 |
| - | 4 | 438/166 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/04/17 18:22 |
| - | 289 | el and transparent and (thin adj film and transistor) and (257/\$.ccls. or 438/\$.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/10/23 19:01 |
| - | 1 | "6235561".PN. | USPAT | 2002/04/18 11:45 |
| - | 1 | "5446562".PN. | USPAT | 2002/04/18 15:01 |

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| | 262 | 257/57 and ((silicon adj oxide) same thickness) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 18:36 |
| | 6 | 257/57 and ((protective adj insulating adj film) same thickness) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/18 17:57 |
| | 12 | 257/59 and ((protective adj insulating adj film) same thickness) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/18 16:02 |
| | 10 | 257/72 and ((protective adj insulating adj film) same thickness) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 13:16 |
| | 2 | 257/57 and ((protective adj insulating adj film) same defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 15:11 |
| | 6 | 257/59 and ((protective adj insulating adj film) same defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/18 17:59 |
| | 3 | 257/72 and ((protective adj insulating adj film) same defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/18 17:59 |
| | 7 | TFT and ((protective adj insulating adj film) same (amorphous adj silicon)) and (257/\$.cccls. or 438/\$.cccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 12:58 |
| | 6 | TFT and ((protective adj insulating adj film) WITH (amorphous adj silicon)) and (257/\$.cccls. or 438/\$.cccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 12:59 |
| | 6 | 257/72 and ((protective adj insulating adj film) same amorphous) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 13:17 |
| | 10 | 257/59 and ((protective adj insulating adj film) same amorphous) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 13:17 |
| | 8 | 257/57 and ((protective adj insulating adj film) same amorphous) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 13:17 |
| | 38 | 257/72 and ((silicon adj oxide) same defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 15:12 |
| | 37 | 257/59 and ((silicon adj oxide) same defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/04/22 15:12 |

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| | 24 | 257/57 and ((silicon adj oxide) same defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 15:19 |
| | 837 | 257/72 and transparent and (thin adj film adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 11:17 |
| | 51 | 257/72 and transparent and (thin adj film adj transistor) and (thickness near (silicon adj nitride)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 11:37 |
| | 1 | 257/72 and transparent and (thin adj film adj transistor) and ((protective adj insulating adj film) near2 ("100" nm)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 11:40 |
| | 11 | 257/72 and transparent and (thin adj film adj transistor) and ((protective adj insulating adj film) with ("100" nm)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 17:45 |
| | 1 | "6046479".PN. | USPAT | 2002/10/23 13:32 |
| | 5 | 257/59 and ((protective adj insulating adj film) with defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 15:50 |
| | 2 | 257/72 and ((protective adj insulating adj film) with defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 15:49 |
| | 6 | 257/\$.ccls. and ((protective adj insulating adj film) with defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/01 16:47 |
| | 2 | 438/\$.ccls. and ((protective adj insulating adj film) with defect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 16:06 |
| | 17 | (protective adj insulating adj film) with defect | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 16:10 |
| | 6 | 257/72 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (alignment adj layer) and (counter adj substrate) and (counter adj electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 18:34 |
| | 566 | (organic adj 'EL') and (thin adj film adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 19:02 |
| | 114 | (organic adj 'EL') and (thin adj film adj transistor) and 257/\$.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 19:06 |
| | 7 | (organic adj 'EL') and (cathode adj layer) and (anode adj layer) and (thin adj film adj transistor) and 257/\$.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/23 19:07 |

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| - | 7 | 257/\$.ccls. and ((amorphous adj film) with oxidation) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/11/01 16:58 |
| - | 7 | 257/\$.ccls. and (oxidation with (amorphous adj film)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/11/01 17:10 |
| - | 1 | (surface adj oxidation) near2 (amorphous adj film) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/11/01 17:44 |
| - | 20 | (thermal adj oxidation) SAME (amorphous adj film) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/10 16:35 |
| - | 102 | (surface near2 (amorphous adj silicon)) with oxidation | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/11/03 10:09 |
| - | 74 | (surface near2 (amorphous adj silicon)) near5 oxidation | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/11/03 10:44 |
| - | 3 | nitride with ((surface near2 (amorphous adj silicon)) near5 oxidation) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/11/03 10:59 |
| - | 1 | nitride near5 ((surface near2 (amorphous adj silicon)) near5 oxidation) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/11/03 10:59 |
| - | 19 | surface with (amorphous adj film) with oxidation | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/11 08:33 |
| - | 245 | 438/150 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/11 08:38 |
| - | 193 | 438/150 and (TFT or (thin adj film adj transistor)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/11 10:24 |
| - | 787 | 438/151 and (TFT or (thin adj film adj transistor)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/11 10:26 |
| - | 108 | 438/151 and (TFT or (thin adj film adj transistor)) and (surface with (amorphous adj silicon) with (oxide or oxidation)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/11 10:30 |
| - | 233 | 438/151 and (TFT or (thin adj film adj transistor)) and ((amorphous adj silicon) with (oxide or oxidation)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/11 10:32 |

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| - | 113 | 438/151 and (TFT or (thin adj film adj transistor)) and ((amorphous adj silicon) with (oxide or oxidation)) and polysilicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/11 10:33 |
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